Symmetrical Gate Turn-Off Thyristor Type SA20AP1200UT



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Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V _{DRM}	Repetitive peak off-state voltage, (note 1)	2000	V
V _{RSM}	Non-repetitive peak off-state voltage, (note 1)	2100	V
V _{RRM}	Repetitive peak reverse voltage	300	V
V _{RSM}	Non-repetitive peak reverse voltage	300	V
note 1)	$V_{GK} = -2V$		

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I _{TGQ}	Peak turn-off current (note 1)	1200	А
L _S	Snubber loop impedance, $I_{TM} = I_{TGQ}$ (note 1)	0.3	μΗ
I _{T(AV)M}	Mean on-state current, T _{sink} = 55°C, (note 2)	670	А
I _{T(RMS)}	Nominal RMS on-state current, T _{sink} = 25°C (note 2)	1340	А
I _{TSM}	Peak non-repetitive surge current t _p = 10ms	10.5	kA
I _{TSM2}	Peak non-repetitive surge current (note 3)	19	kA
l ² t	l ² t capacity for fusing t _p = 10ms	$550 \cdot 10^{3}$	A ² s
(di/dt) _{cr}	Critical rate of rise of on-state current, (note 4)	1000	A/µs
P _{FGM}	Peak forward gate power	210	W
P _{RGM}	Peark reverse gate power	8	kW
I _{FGM}	Peak forward gate current	140	А
V _{RGM}	Peak reverse gate voltage (note 5)	18	V
t _{off}	Minimum permissible off-time, $I_{TM} = I_{TGQ}$ (note 1)	80	μs
t _{on}	Minimum permissible off-time	20	μs
Т _{јор}	Operating temperature range	-40 to +125	°C
T _{stg}	Storage temperature range	-40 to +150	°C
note 1)	$\rm T_{j}$ = 125°C, $\rm V_{D}$ = 80%V_{DM}, V_{DM} \leq V_{DRM}, di_{GQ}/dt = 20A/µs, $\rm C_{S}$ = 3µF		
note 2)	Double-side cooled, single phase, 50Hz, 180° half-sinewave.		
note 3)	Half-sinewave, t _p = 2ms		
note 4)	For di/dt > 1000A/µs please consult factory.		
note 5)	May exceed this value during turn-off avalanche period.		

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Characteristics

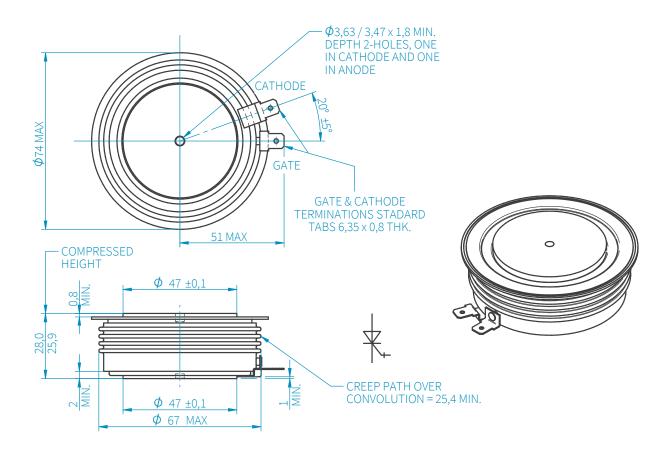
	PARAMETER	TEST CONDITIONS	MIN	ТҮР	МАХ	UNITS
V _{TM}	Maximum peak on-state voltage	I _G = 2A, I _T = 1200A	-	3.0	3.3	V
IL.	Latching current	T _i = 25°C	-	15	-	А
Ι _Η	Holding current	1 ₁ - 25 C	-	15	-	А
(dv/dt) _{cr}	Critical rate of rise of off-state voltage	$V_{D} = 80\% V_{DRM}, V_{GR} = -2V$	1000	-	-	V/µs
I _{DRM}	Peak off-state current	Rated V_{DRM} , $V_{GR} = -2V$	-	-	50	mA
I _{RRM}	Peak reverse current	Rated V _{RRM}	-	-	100	mA
I _{GKM}	Peak negative gate leakage current	$V_{GR} = -16V$	-	-	200	mA
		$T_j = -40^{\circ}C$, $V_D = 25V$, $R_L = 25m\Omega$	-	1.0	-	V
V _{GT}	Gate trigger voltage	$T_j = 25^{\circ}C, V_D = 25V, R_L = 25m\Omega$	-	0.9	-	V
		$T_{j} = 125^{\circ}C, V_{D} = 25V, R_{L} = 25m\Omega$	-	0.8	-	V
		$T_{j} = -40^{\circ}$ C, $V_{D} = 25$ V, $R_{L} = 25$ m Ω	-	3.0	8.0	А
I _{GT}	Gate trigger current	$T_{j} = 25^{\circ}C, V_{D} = 25V, R_{L} = 25m\Omega$	-	0.6	2.5	A
		$T_{j} = 125^{\circ}C, V_{D} = 25V, R_{L} = 25m\Omega$	-	60	500	mA
t _d	Delay time	(note 2)	-	1.0	-	μs
t _{gt}	Turn-on time	Conditions as for $t_d, (10\% l_{GM} \mbox{ to } 10\% V_D)$	-	3.0	7.0	μs
t _f	Fall time	(note 3)	-	0.8	-	μs
t _{gq}	Turn-off time	Conditions as for $t_f,(10\% I_{GQ}$ to $10\% I_{TGQ})$	-	12	13	μs
I _{GQ}	Turn-off gate current	Conditions of fact	-	250	-	А
Q _{GQ}	Turn-off gate charge	Conditions as for t _f	-	1600	2000	mC
t _{tail}	Tail time	Conditions as for t _f , (10%I _{TGQ} to I _{TGQ} < 1A)	-	40	60	μs
t _{gw}	Gate off-time (note 4)	Conditions as for t _f	150	-	-	μs
		Double side cooled	-	-	0.027	K/W
R _{thJK}	Thermal resistance, junction to sink	Cathode side cooled	-	-	0.070	K/W
		Anode side cooled	-	-	0.045	K/W
F	Mounting force	(note 5)	15	-	25	kN
Wt	Weight		-	480	-	g
note 1)	Unless otherwise indicated T _j = 125°C					
note 2)	, V _D = 50%V _{DRM} , I _{TGQ} = 1200A, I _{GM} = 40A, di _G /dt = 20A/μs, T _j = 25°C, di/dt = 300A/μs, (10%I _{GM} to 90%V _D)					
note 3)	$V_{\rm D} = 80\% V_{\rm DRM}$, $I_{\rm TGO} = 1200$ A, $C_{\rm S} = 3\mu$ F, di _G /dt = 40A/ μ s, $V_{\rm GR} = -16$ V, (90% $I_{\rm TGO}$ to 10% $V_{\rm D}$)					
note 4)	The gate off-time is the period during which the gate circuit is required to remain low impedance to allow for the pas- sage of tail current.					
note 5)	For other clamping forces, consult factory	/.				

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